

/ Descriptions

WR0<5 ММ Ё SQS æ Ñ ç s ll 1 Silicon PNP transistor in a TO-92 Plastic Package.

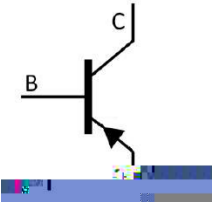
/ Features

лъ 5VF464: Ы ´
Complementary pair with 2SC1317.

/ Applications

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AF output amplifier and driver.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ hFE Classifications & Marking

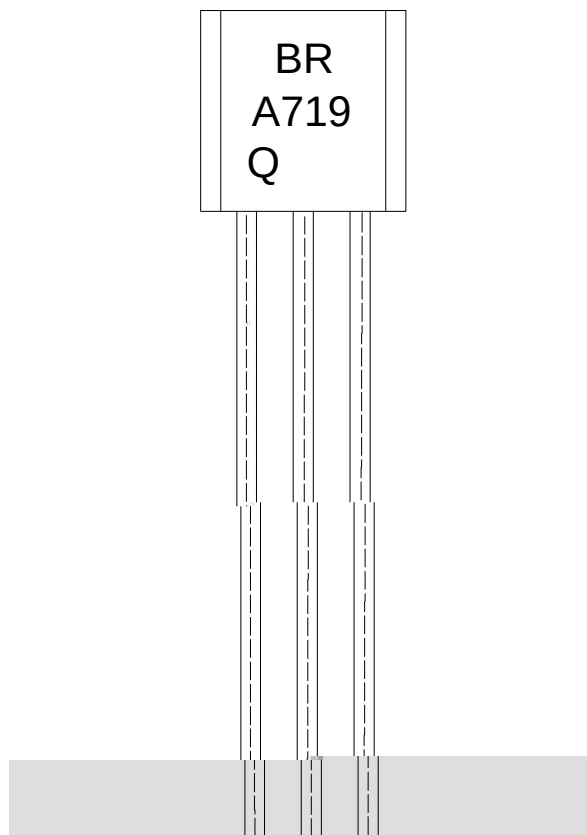
h _{FE} Classifications Symbol	Q	R	S
h _{FE} Range	85~170	120~240	170~340

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Current – Continuous(Pulse)	I_{CP}	-1.0	A
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10mA$ $I_B = 0$	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20V$ $I_E = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -10V$ $I_C = -150mA$	85		340	
	$h_{FE(2)}$	$V_{CE} = -10V$ $I_C = -500mA$	40			

Collector to Emitter Saturation

/ Marking Instructions



б " X

EU:

№ 3^М Пб

D: 4< X

№ 3^N 3^N

T:

№ h_{FE}^с 6 Пб

---- X

№ 1 f ъ^N Пб 1 ф 1 f ъ^N ψ p

Note:

BR:

Company Code.

A719:

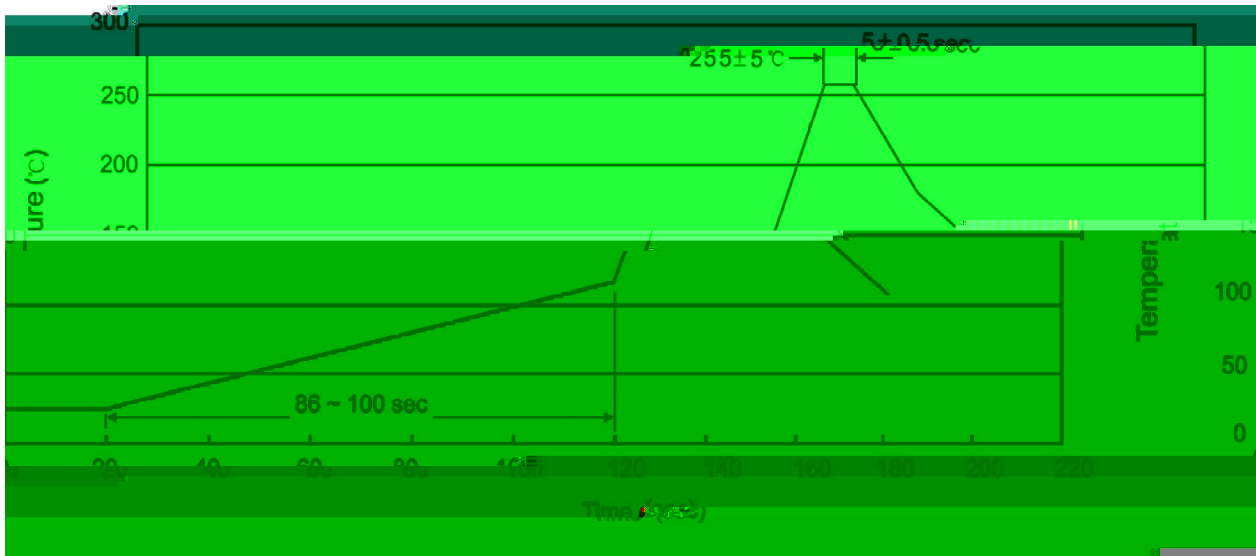
Product Type.

Q:

h_{FE} Classifications Symbol

***:

Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)


说明

1. 预加热: 25~150℃, 时间: 60~90sec;
2. 峰值温度: 255±5℃, 时间: 5±0.5sec;
3. 冷却速度: 2~10℃/sec.

Note:

1. Preheating: 25~150℃, Time: 60~90sec.
2. Peak Temp.: 255±5℃, Duration: 5±0.5sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

温度: 270±5℃

时间: 10±1 sec.

Temp: 270±5

Time: 10±1 sec

/ Packaging SPEC.

包装形式 / BULK

每包数量